# MSKSEMI 美森科













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# BT137S-XXXE(MS)

**Product specification** 





#### **DESCRIPTION**

The BT137S-XXXE(MS) SCR series with the parallel resistor between Gate and Cathode are especially recommended for use on straight hair, igniter, anion generator, etc.

#### **MAIN FEATURES**

Symbol	Value	Unit
I <sub>T(RMS)</sub>	8	А
VDRM /VRRM	600/800	V

#### **Reference News**

PACKAGE OUTLINE	Pin Configuration	Marking	
1 2 SERVICIONOLETORS	O T2(2) O T1(1)	MSKSEMI BT137S-600E MS XXX	MSKSEMI BT137S-800E MS XXX
3		BT137S-600E(MS)	BT137S-800E(MS)

**Notes :XXX** represents the order code.

#### **ABSOLUTE MAXIMUM RATINGS**

Parameter		Symbol	Value	Unit
Storage junction temperature range		Tstg	-40-150	$^{\circ}$ C
Operating junction temperature range		Tj	-40-125	$^{\circ}$ C
Repetitive peak off-state voltage(T <sub>j</sub> =25	5℃)	VDRM	600/800	V
Repetitive peak reverse voltage(T <sub>j</sub> =25	℃)	VRRM	600/800	V
RMS on-state current(TC=103℃)		I <sub>T(RMS)</sub>	8	А
Non repetitive surge peak on-state current (full cycle, F=50Hz)		Ітѕм	65	А
Pt value for fusing (tp=10ms)		Pt	21	A <sup>2</sup> s
Peak gate current		l <sub>GM</sub>	2	А
Critical rate of rise of on-state		117.16	50	Δ /
current(I <sub>G</sub> =2×I <sub>GT</sub> )		dl/dt	10	A/µs
Average gate power dissipation		P <sub>G(AV)</sub>	0.5	W
Peak gate power		Рдм	5	W



# **ELECTRICAL CHARACTERISTICS** (T<sub>j</sub>=25 °C unless otherwise specified)

Symbol	Test Condition	Quadrant		Value	Unit
		I - II -III	MAN	10	^
lgт	V <sub>D</sub> =12V RL=30 Ω	IV	MAX	25	mA
V <sub>GT</sub>		ALL	MAX	1.3	V
V <sub>GD</sub>	V <sub>D</sub> =V <sub>DRM</sub> T <sub>j</sub> =125°C R <sub>L</sub> =3.3KΩ	ALL	MIN	0.2	V
		I -III	MAN	20	т Л
l.	lg=1.2Igт	II-IV	MAX	30	mA
Ін	h=100mA		MAX	15	mA
dV/dt	V <sub>D</sub> =2/3V <sub>DRM</sub> Gate Open Tj=125℃	l	MIN	50	V/µs

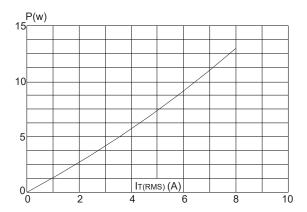
## STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
Vтм	Ітм=10Atp=380µs	Tj=25℃	1.6	V
IDRM	N N N	Tj=25℃	5	μA
IRRM	VD=VDRM VR=VRRM	Tj=125℃	1	mA

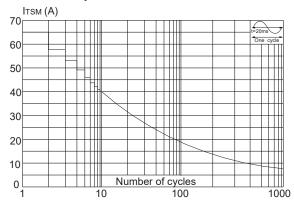
#### THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
Rth(j-c)	junction to case(AC)	2.1	°C/W
Rth(j-a)	junction to ambient	70	°C/W

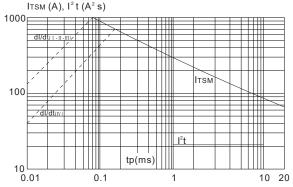
**FIG.1:** Maximum power dissipation versus RMS on-state current



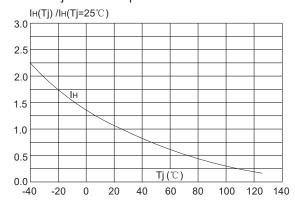
**FIG.3:** Surge peak on-state current versus number of cycles



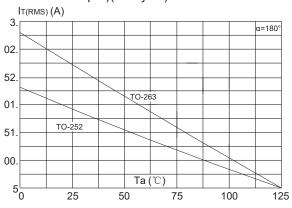
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<20ms, and corresponging value of  $I^2t$  ( I - II - III : dI/dt < 50A/ $\mu$ s; IV:dI/dt < 10A/ $\mu$ s)



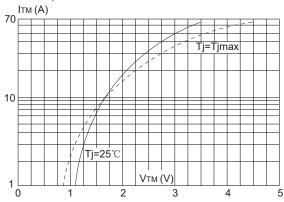
**FIG.7:** Relative variations of holding current versus junction temperature



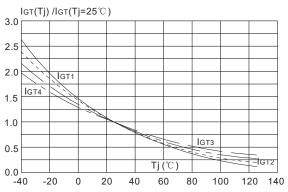
**FIG.2:** RMS on-state current versus ambient temperature (printed circuit board FR4,copper thickness:35µm)(full cycle)



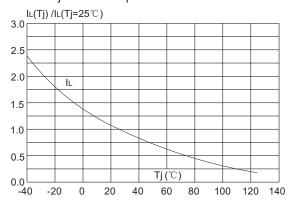
**FIG.4:** On-state characteristics (maximum values)



**FIG.6:** Relative variations of gate trigger current versus junction temperature

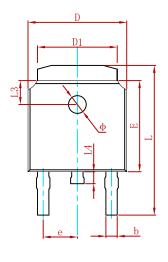


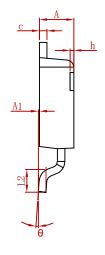
**FIG.8:** Relative variations of latching current versus junction temperature

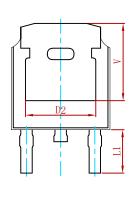




## PACKAGE MECHANICAL DATA

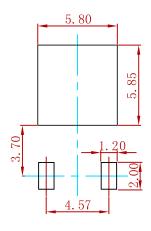






Cumbal	Dimensions In Millimeters		Dimension	s In Inches
Symbol	Min.	Max.	Min.	Max.
Α	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
С	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830	REF.	0.190 REF.	
E	6.000	6.200	0.236	0.244
е	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900	REF.	0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600	REF.	0.063	REF.
L4	0.600	1.000	0.024	0.039
Ф	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250	5.250 REF.		REF.

# **Suggested Pad Layout**



#### Note:

- 1. Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
BT137S-XXXE(MS)	TO-252	2500



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